

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS E6

600V CoolMOS™ E6 Power Transistor
IPx60R190E6

Data Sheet

Rev. 2.0, 2010-05-03
Final

Industrial & Multimarket

600V CoolMOS™ E6 Power Transistor

IPP60R190E6, IPA60R190E6
IPW60R190E6

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ E6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC¹⁾ qualified, Pb-free plating, Halogen free

Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

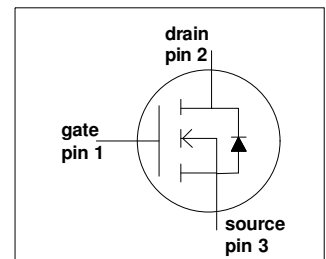
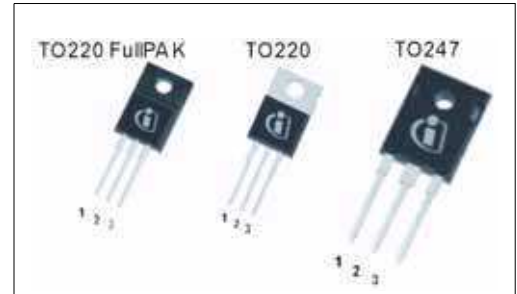


Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|----------------------|-------|------------|
| $V_{DS} @ T_{j,max}$ | 650 | V |
| $R_{DS(on),max}$ | 0.19 | Ω |
| $Q_{g,typ}$ | 63 | nC |
| $I_{D,pulse}$ | 59 | A |
| $E_{oss} @ 400V$ | 5.2 | μJ |
| Body diode di/dt | 500 | A/ μs |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|------------------|---------|---|
| IPW60R190E6 | PG-TO247 | 6R190E6 | IFX CoolMOS Webpage IFX Design tools |
| IPP60R190E6 | PG-TO220 | | |
| IPA60R190E6 | PG-TO220 FullPAK | | |

1) J-STD20 and JESD22

Table of Contents

| | | |
|---|---|----|
| 1 | Description | 2 |
| | Table of Contents | 3 |
| 2 | Maximum ratings | 4 |
| 3 | Thermal characteristics | 5 |
| 4 | Electrical characteristics | 6 |
| 5 | Electrical characteristics diagrams | 8 |
| 6 | Test circuits | 13 |
| 7 | Package outlines | 14 |
| 8 | Revision History | 17 |

2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified.

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|----------------|--------|------|------|------------------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | - | - | 20.2 | A | $T_C = 25\text{ °C}$ |
| | | | | 12.8 | | $T_C = 100\text{ °C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 59 | A | $T_C = 25\text{ °C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 418 | mJ | $I_D = 3.4\text{ A}, V_{DD} = 50\text{ V}$ (see table 20) |
| Avalanche energy, repetitive | E_{AR} | - | - | 0.63 | | $I_D = 3.4\text{ A}, V_{DD} = 50\text{ V}$ |
| Avalanche current, repetitive | I_{AR} | - | - | 3.4 | A | |
| MOSFET dv/dt ruggedness | dv/dt | - | - | 50 | V/ns | $V_{DS} = 0 \dots 480\text{ V}$ |
| Gate source voltage | V_{GS} | -20 | - | 20 | V | static |
| | | -30 | | 30 | | AC ($f > 1\text{ Hz}$) |
| Power dissipation for TO-220, TO-247 | P_{tot} | - | - | 151 | W | $T_C = 25\text{ °C}$ |
| Power dissipation for TO-220 FullPAK | P_{tot} | - | - | 34 | | |
| Operating and storage temperature | T_j, T_{stg} | -55 | - | 150 | °C | |
| Mounting torque TO-220, TO-247 | | - | - | 60 | Ncm | M3 and M3.5 screws |
| Mounting torque TO-220 FullPAK | | | | 50 | | M2.5 screws |
| Continuous diode forward current | I_S | - | - | 17.5 | A | $T_C = 25\text{ °C}$ |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | - | - | 59 | A | $T_C = 25\text{ °C}$ |
| Reverse diode dv/dt ³⁾ | dv/dt | - | - | 15 | V/ns | $V_{DS} = 0 \dots 400\text{ V}, I_{SD} \leq I_D,$ $T_j = 25\text{ °C}$ |
| Maximum diode commutation speed ³⁾ | di/dt | | | 500 | A/ μs | (see table 21) |

1) Limited by $T_{j,max}$. Maximum duty cycle $D = 0.75$

2) Pulse width t_p limited by $T_{j,max}$

3) Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics TO-220 (IPP60R190E6), TO-247 (IPW60R190E6)

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|---------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 0.83 | °C/W | leaded |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 62 | | |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | °C | 1.6 mm (0.063 in.) from case for 10 s |

Table 4 Thermal characteristics TO-220 FullPAK (IPA60R190E6)

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|---------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3.7 | °C/W | leaded |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 80 | | |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | °C | 1.6 mm (0.063 in.) from case for 10 s |

4 Electrical characteristics

Electrical characteristics, at $T_J=25\text{ °C}$, unless otherwise specified.

Table 5 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|------|-------|---------------|--|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 600 | - | - | V | $V_{GS}=0\text{ V}$, $I_D=0.25\text{ mA}$ |
| Gate threshold voltage | $V_{GS(th)}$ | 2.5 | 3 | 3.5 | | $V_{DS}=V_{GS}$, $I_D=0.63\text{ mA}$ |
| Zero gate voltage drain current | I_{DSS} | - | - | 1 | μA | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=25\text{ °C}$ |
| | | - | 10 | - | | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=150\text{ °C}$ |
| Gate-source leakage current | I_{GSS} | - | - | 100 | nA | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 0.17 | 0.190 | Ω | $V_{GS}=10\text{ V}$, $I_D=9.5\text{ A}$, $T_J=25\text{ °C}$ |
| | | - | 0.44 | - | | $V_{GS}=10\text{ V}$, $I_D=9.5\text{ A}$, $T_J=150\text{ °C}$ |
| Gate resistance | R_G | - | 6 | - | Ω | $f=1\text{ MHz}$, open drain |

Table 6 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition | |
|--|--------------|--------|------|------|------|---|--|
| | | Min. | Typ. | Max. | | | |
| Input capacitance | C_{iss} | - | 1400 | - | pF | $V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$ | |
| Output capacitance | C_{oss} | - | 85 | - | | | |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | - | 56 | - | | | $V_{GS}=0\text{ V}$, $V_{DS}=0\dots480\text{ V}$ |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | - | 266 | - | | | $I_D=\text{constant}$, $V_{GS}=0\text{ V}$ $V_{DS}=0\dots480\text{ V}$ |
| Turn-on delay time | $t_{d(on)}$ | - | 12 | - | ns | $V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=9.5\text{ A}$, $R_G=3.4\text{ }\Omega$ (see table 19) | |
| Rise time | t_r | - | 10 | - | | | |
| Turn-off delay time | $t_{d(off)}$ | - | 90 | - | | | |
| Fall time | t_f | - | 8 | - | | | |

1) $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

2) $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 7 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|----------------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 7.6 | - | nC | $V_{DD}=480\text{ V}$, $I_D=9.5\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge | Q_{gd} | - | 32 | - | | |
| Gate charge total | Q_g | - | 63 | - | | |
| Gate plateau voltage | V_{plateau} | - | 5.4 | - | V | |

Table 8 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | - | 0.9 | - | V | $V_{GS}=0\text{ V}$, $I_F=9.5\text{ A}$, $T_j=25\text{ °C}$ |
| Reverse recovery time | t_{rr} | - | 430 | - | ns | $V_R=400\text{ V}$, $I_F=9.5\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ (see table 22) |
| Reverse recovery charge | Q_{rr} | - | 6.9 | - | μC | |
| Peak reverse recovery current | I_{rrm} | - | 30 | - | A | |

5 Electrical characteristics diagrams

Table 9

| Power dissipation TO-220, TO-247 | Power dissipation TO-220 FullPAK |
|-------------------------------------|-------------------------------------|
| | |
| $P_{tot} = f(T_C)$ | $P_{tot} = f(T_C)$ |

Table 10

| Max. transient thermal impedance TO-220, TO-247 | Max. transient thermal impedance TO-220 FullPAK |
|--|--|
| | |
| $Z_{(thJC)} = f(t_p)$; parameter: $D = t_p / T$ | $Z_{(thJC)} = f(t_p)$; parameter: $D = t_p / T$ |

Electrical characteristics diagrams

Table 11

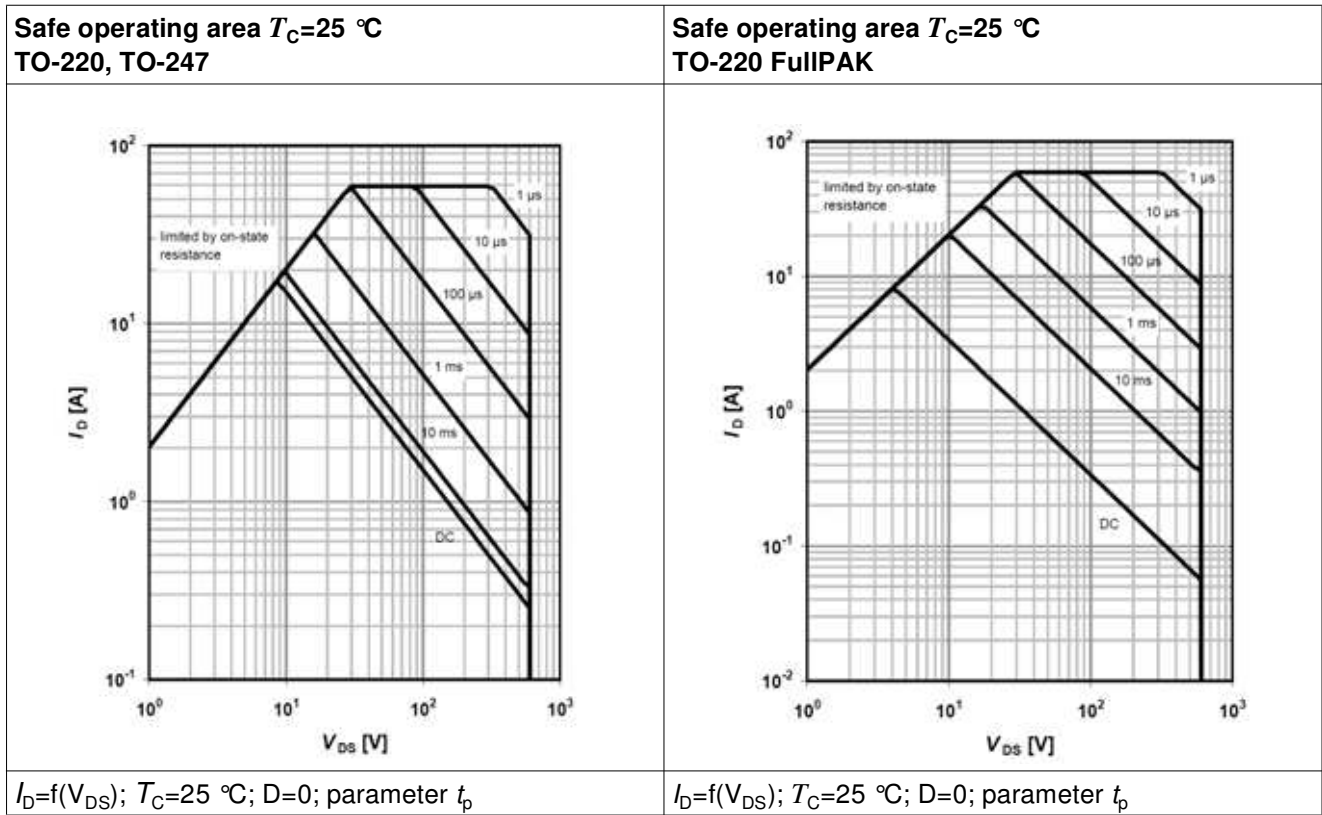


Table 12

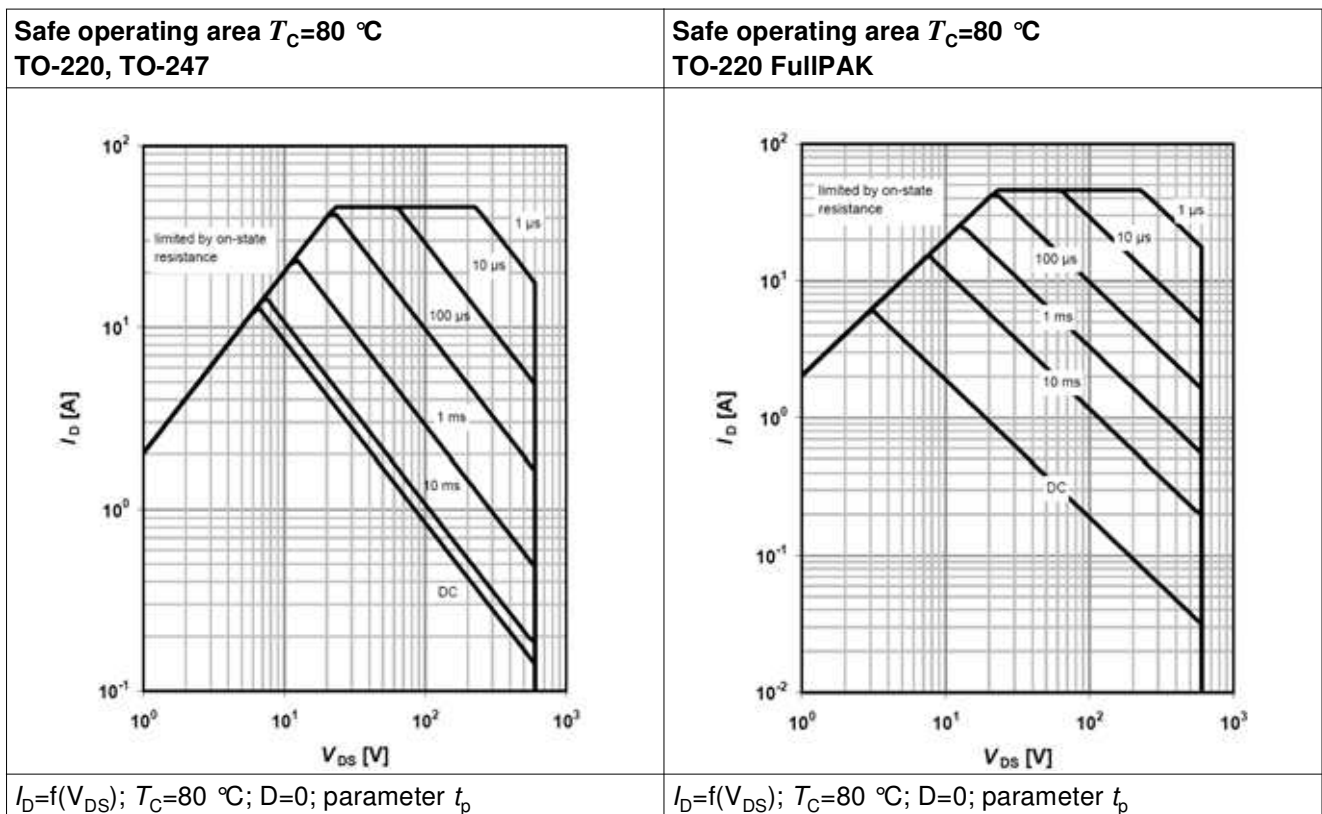


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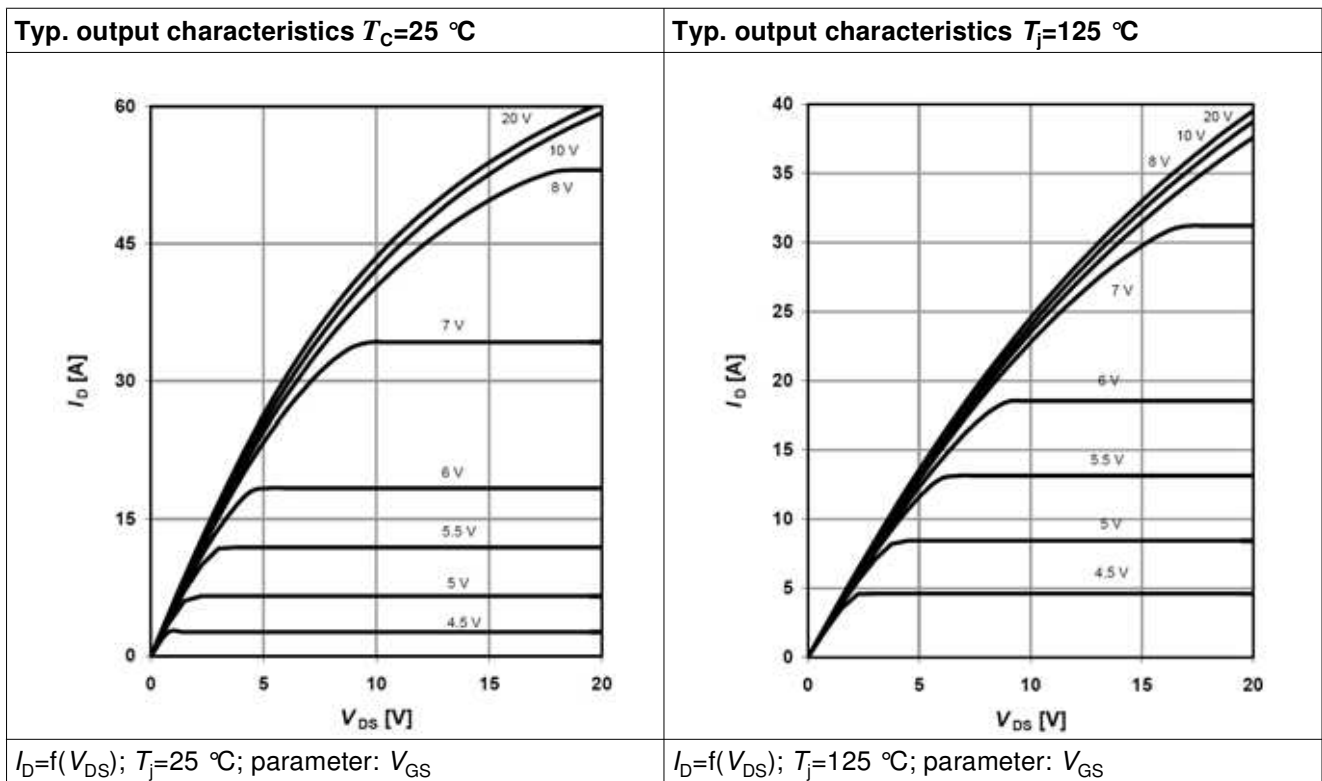


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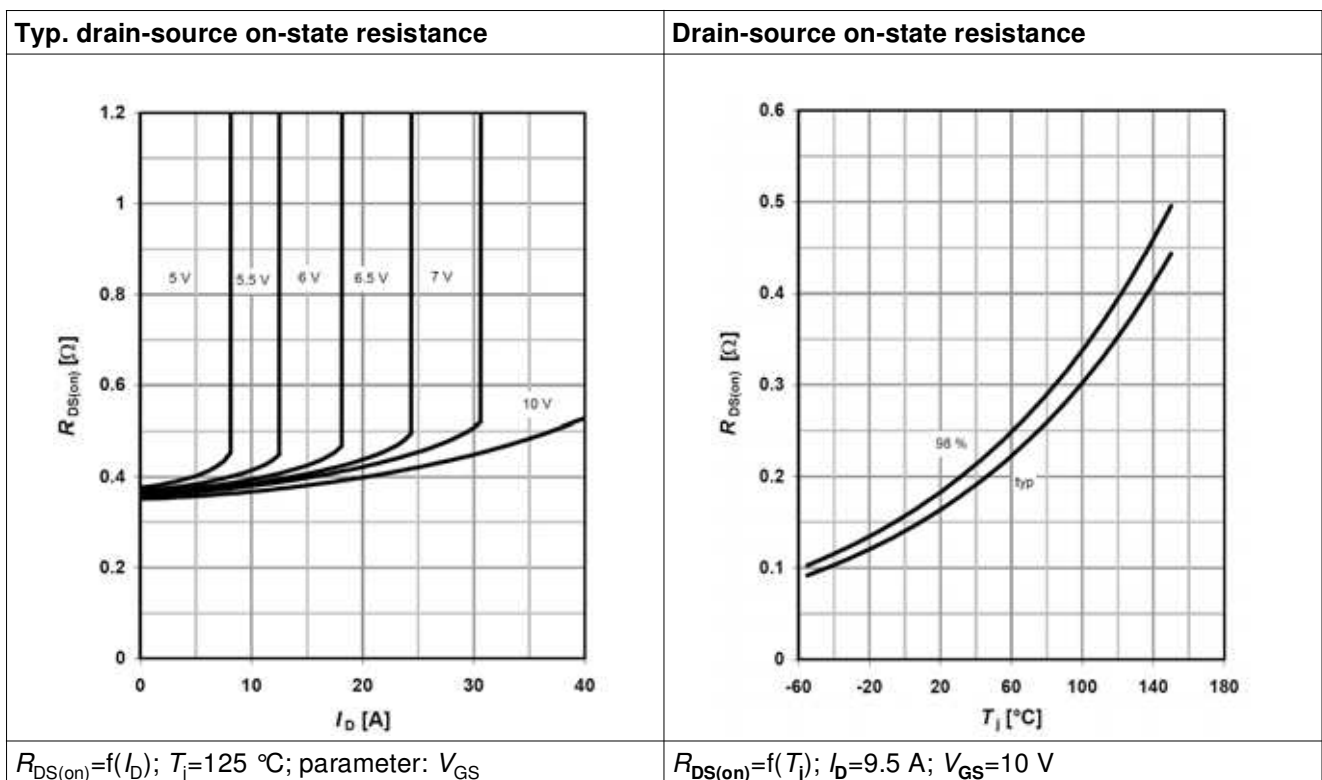


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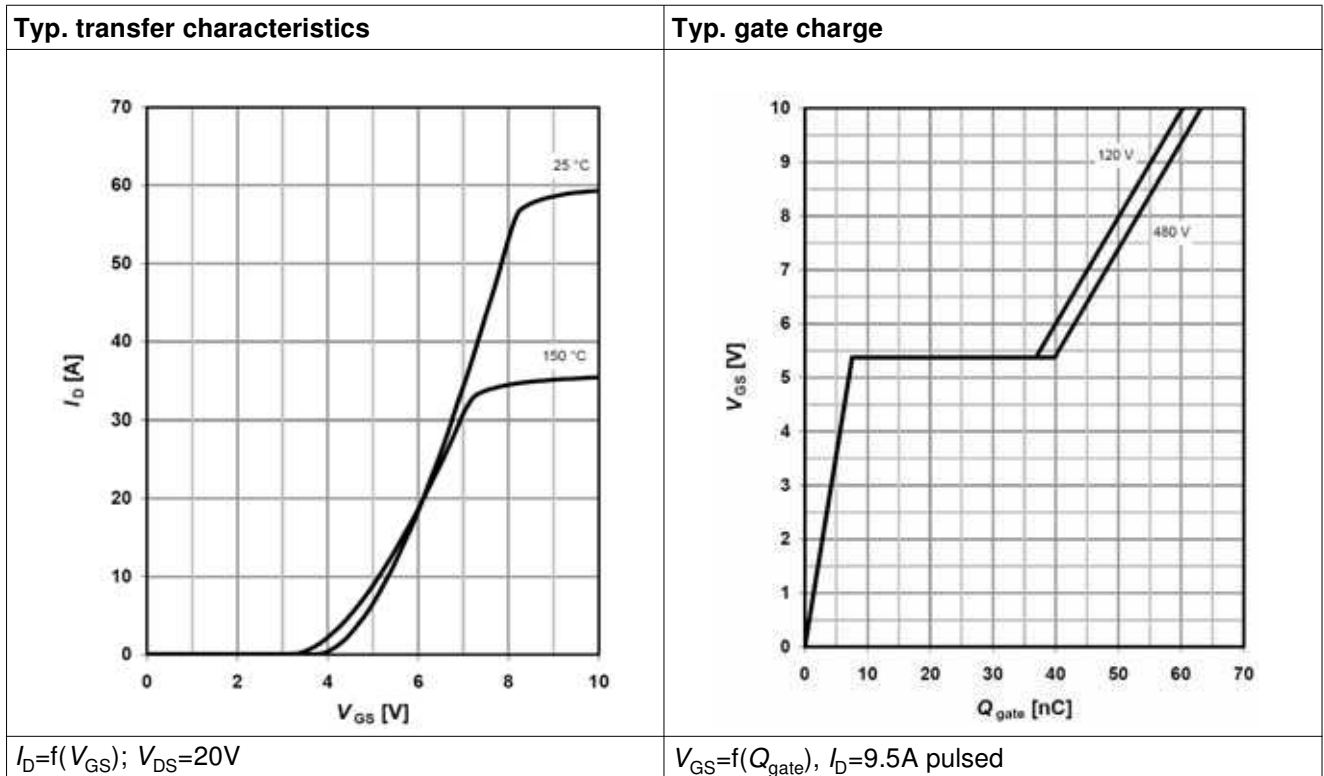


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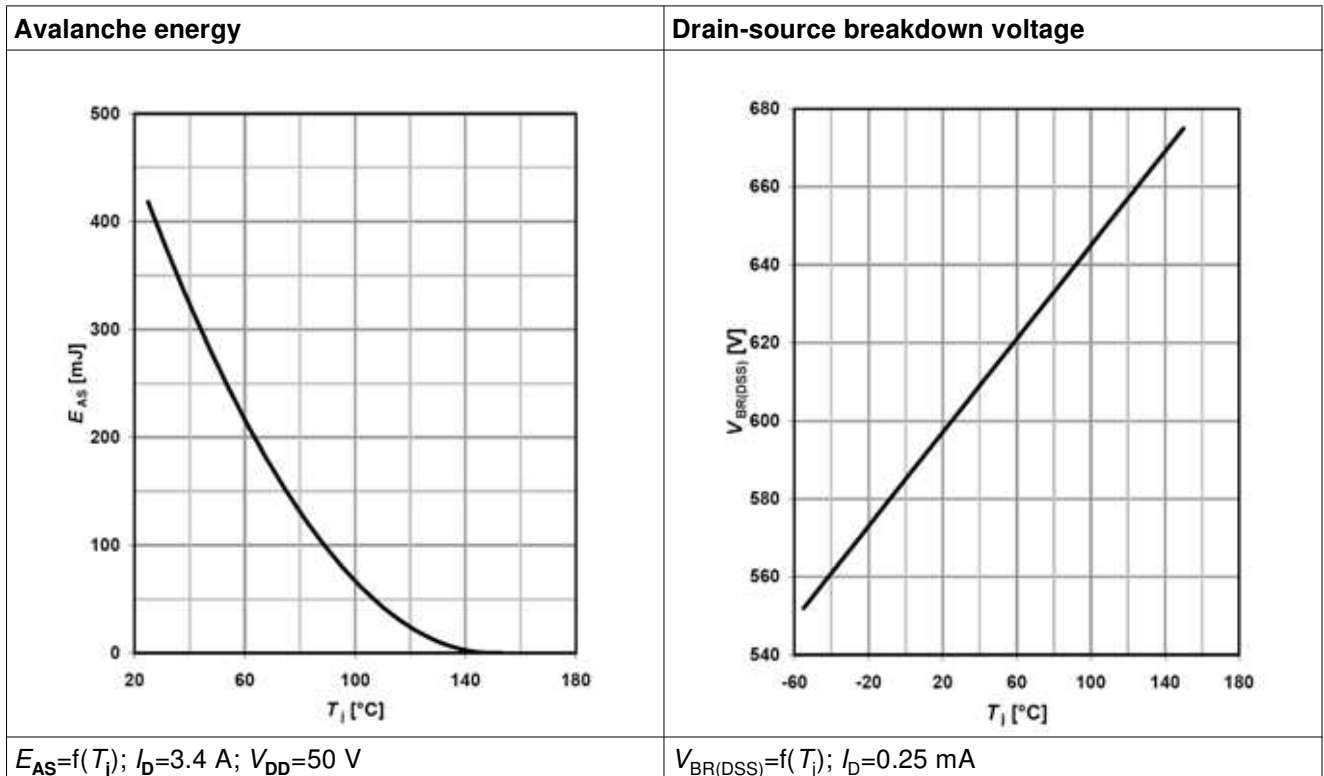


Table 17

| Typ. capacitances | Typ. C_{oss} stored energy |
|--|------------------------------|
| | |
| $C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$ | $E_{oss}=f(V_{DS})$ |

Table 18

| Forward characteristics of reverse diode |
|--|
| |
| $I_F=f(V_{SD}); \text{parameter: } T_j$ |

6 Test circuits

Table 19 Switching times test circuit and waveform for inductive load

| Switching times test circuit for inductive load | Switching time waveform |
|---|-------------------------|
| | |

Table 20 Unclamped inductive load test circuit and waveform

| Unclamped inductive load test circuit | Unclamped inductive waveform |
|---------------------------------------|------------------------------|
| | |

Table 21 Test circuit and waveform for diode characteristics

| Test circuit for diode characteristics | Diode recovery waveform |
|--|-------------------------|
| | |

7 Package outlines

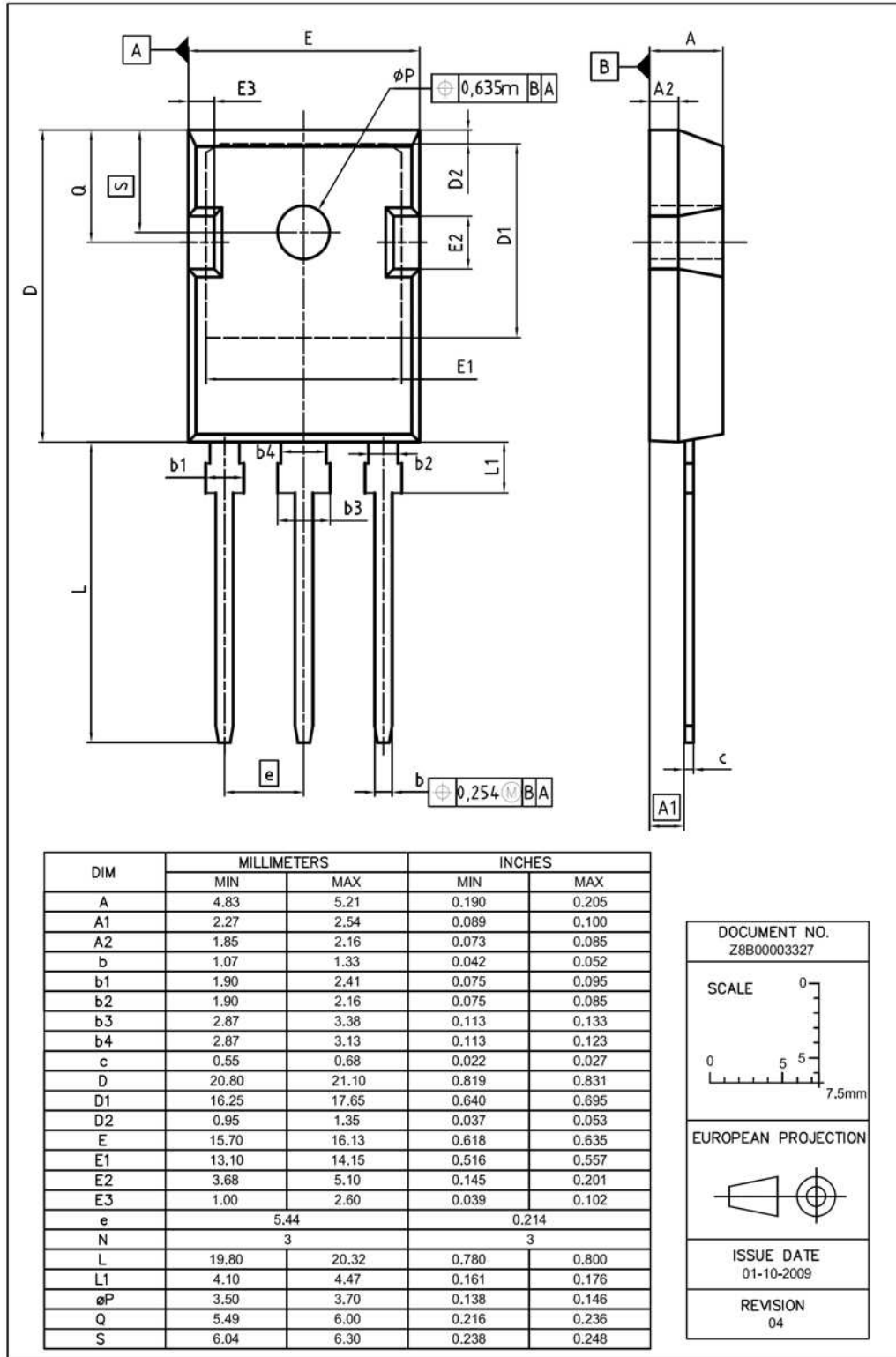
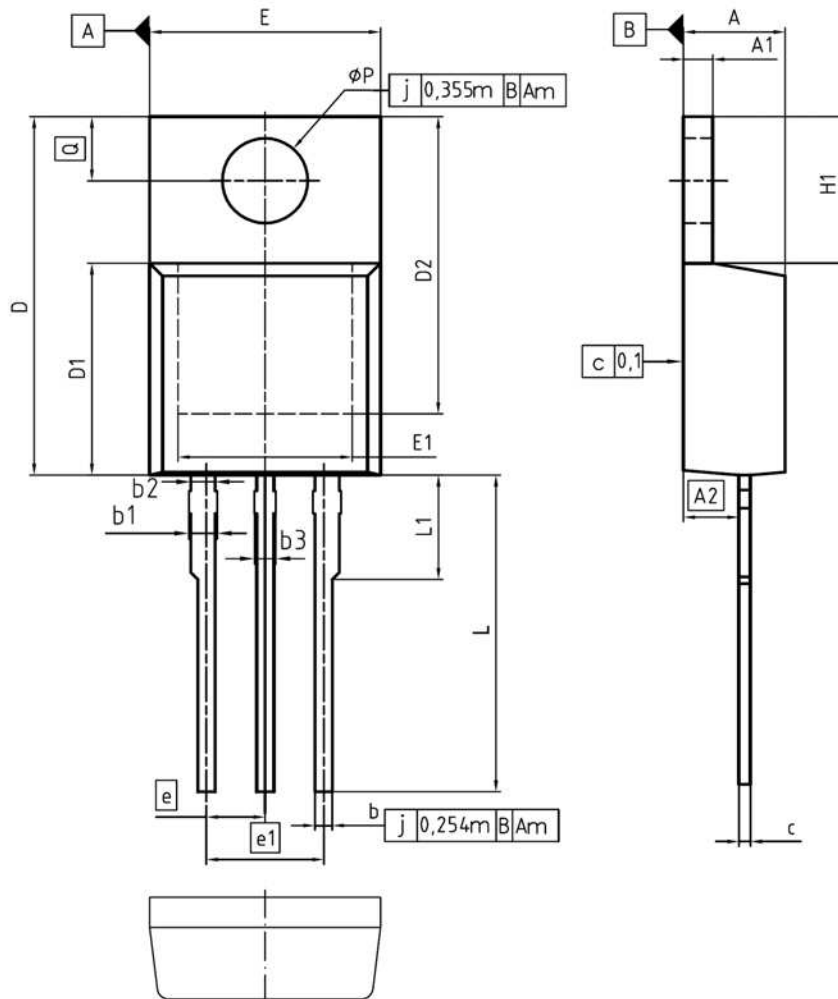


Figure 1 Outlines TO-247, dimensions in mm/inches



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| øP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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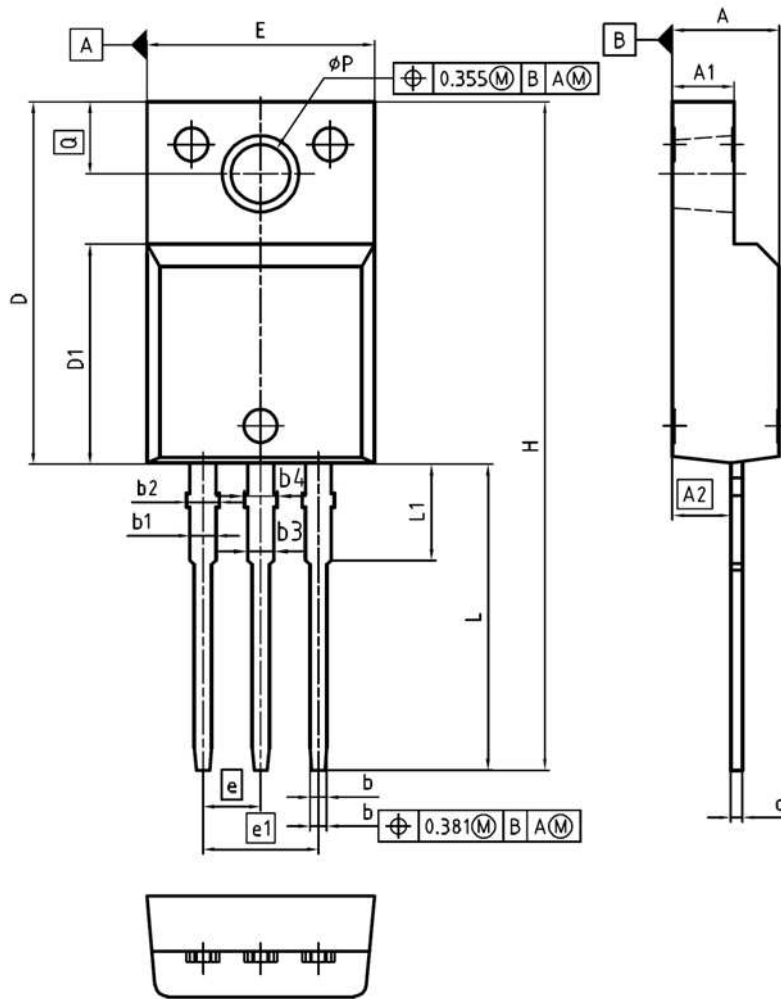
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05

Figure 2 Outlines TO-220, dimensions in mm/inches



| DIM | MILLIMETERS | | INCHES | |
|-------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.55 | 4.85 | 0.179 | 0.191 |
| A1 | 2.55 | 2.85 | 0.100 | 0.112 |
| A2 | 2.42 | 2.72 | 0.095 | 0.107 |
| b | 0.65 | 0.85 | 0.026 | 0.033 |
| b1 | 0.95 | 1.33 | 0.037 | 0.052 |
| b2 | 0.95 | 1.51 | 0.037 | 0.059 |
| b3 | 0.65 | 1.33 | 0.026 | 0.052 |
| b4 | 0.65 | 1.51 | 0.026 | 0.059 |
| c | 0.40 | 0.63 | 0.016 | 0.025 |
| D | 15.85 | 16.15 | 0.624 | 0.636 |
| D1 | 9.53 | 9.83 | 0.375 | 0.387 |
| E | 10.35 | 10.65 | 0.407 | 0.419 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H | 29.45 | 29.75 | 1.159 | 1.171 |
| L | 13.45 | 13.75 | 0.530 | 0.541 |
| L1 | 3.15 | 3.45 | 0.124 | 0.136 |
| phi P | 2.95 | 3.20 | 0.116 | 0.126 |
| Q | 3.15 | 3.50 | 0.124 | 0.138 |

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Figure 3 Outlines TO-220 FullPAK, dimensions in mm/inches

8 Revision History

CoolMOS E6 600V CoolMOS™ E6 Power Transistor

Revision History: 2010-05-03, Rev. 2.0

| Revision | Subjects (major changes since last revision) |
|----------|--|
| 2.0 | Release of final data sheet |
| | |
| | |

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